



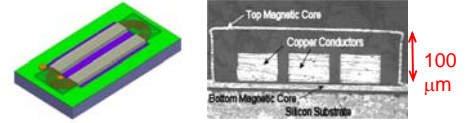
# Electrodeposited multilayer amorphous alloy suitable for high frequency integrated inductors

Paul McCloskey<sup>a</sup>, Brice Jamieson<sup>a</sup>, Terence O'Donnell<sup>a</sup>, Donald Gardner<sup>b</sup>,  
 Michael A. Morris<sup>c</sup>, Saibal Roy<sup>a</sup>  
<sup>a</sup>Tyndall National Institute, Lee Maltings, Prospect Row, Cork.  
<sup>b</sup>Intel Corporation, Santa Clara  
<sup>c</sup>Chemistry Department, University College Cork, College Road, Cork..



## Integration of On-chip Inductors

- On-chip inductors are a major challenge in the move towards monolithic solutions [1].
- A magnetic core in such devices => smaller footprint and less EMI issues [2]
- High switching frequencies => lower values of inductance and capacitance

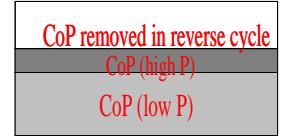
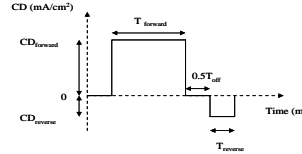


## Background

## Magnetic material properties required

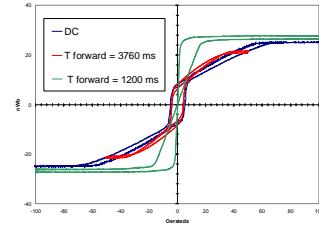
### Low losses at high frequency

- Co-P alloys have high  $\rho$  and low  $H_c$  => low eddy current loss and low hysteresis loss.
- DC plated films exhibit perpendicular anisotropy [3]
- => very low  $\mu$  and high  $H_c$
- For in-plane anisotropy a multi-nano-layer structure of alternating compositions produced by pulse reverse plating [4] or pulse plating at two different current densities [5] is required.
- High P contents used [4], [5] => relatively low saturation magnetisation say 0.5 to 0.6 T



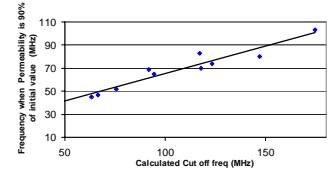
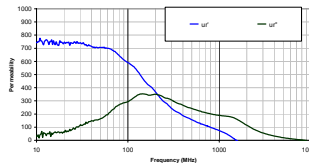
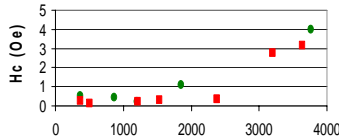
### Temperature stability

- Important because of subsequent processing steps
- Oda et al [6] used small additions of Tungsten (atomic weight =183.8) to improve crystallisation temperature of amorphous FeCoP alloys. However baths containing Tungsten have a tendency to be unstable.
- Rhenium has a high atomic weight 186.2 and can be readily co-deposited with Iron group metals [7].
- The present work is concerned with the characterisation of a novel electrodeposited alloy i.e. CoPRe



## Improved Saturation

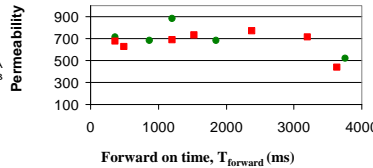
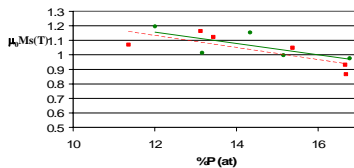
Component	Amount
H <sub>3</sub> PO <sub>3</sub> (g l <sup>-1</sup> )	30
Co CO <sub>3</sub> (g l <sup>-1</sup> )	39.4
CoCl <sub>2</sub> ·6H <sub>2</sub> O (g l <sup>-1</sup> )	181
H <sub>3</sub> PO <sub>4</sub> (g l <sup>-1</sup> )	50
Temperature (°C)	72 +/- 1
Anode	Co (99.5%)
Uniaxial magnetic field	200 Oe



Substrate; silicon wafer with 20 nm Ti and 200 nm Cu seed layer

Plating waveform - Pulse reverse plating  
 $T_{forward} = 870$  to  $3760$  ms,  $CD_{forward} = 170$  mA/cm<sup>2</sup>,  $T_{reverse} = 54$  ms,  $CD_{reverse} = 67$  mA/cm<sup>2</sup>,  $T_{off} = 72$  ms.

Also investigated effect of pH



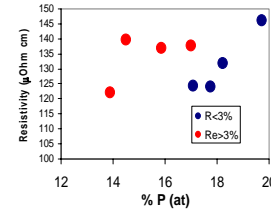
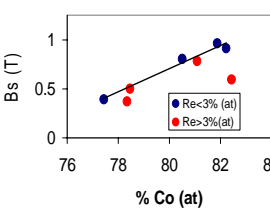
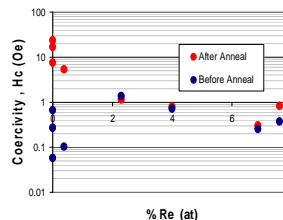
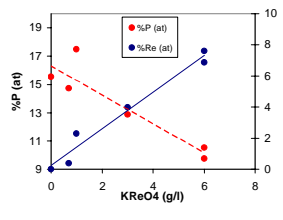
Fall off frequency,  $f_m = 90\%$  of initial value in the range 47 to 103 MHz  
 Cut off frequency for eddy current loss may be estimated using:  
 $f_{cut\ off} = \rho / \pi \mu_r \mu_0 t^2$  where  $\rho$  = resistivity,  $\mu_r$  and  $\mu_0$  are the relative and absolute permeabilities and  $t$  is the thickness  
 Present study; thickness 1.7 to 2.5  $\mu$ m and  $\rho$  116 to 136  $\mu$ Ohm cm

Component	Concentration (g/l)
H <sub>3</sub> PO <sub>3</sub>	65
Co CO <sub>3</sub>	39.4
CoCl <sub>2</sub> ·6H <sub>2</sub> O	181
H <sub>3</sub> PO <sub>4</sub>	50
KReO <sub>4</sub>	0 to 6

Re has a high atomic weight (186.2)

Also investigated effect of pH

## Thermal Stability



## Conclusions

- Optimisation of P content

$\mu_0 Ms$  in the range of 0.9 to 1.2T,  $H_c < 0.5$  Oe,

Permeability of around 700 holding out to a maximum 103 MHz

Resistivity in the range of 116 to 136  $\mu$ Ohm cm,

$H_k$  largely between 12 and 19 Oe (higher values at lower P)

- CoPRe => Improved Thermal Stability

Co<sub>100-x-y</sub> · P<sub>x</sub> · Re<sub>y</sub> where; 9.7 at % < x < 17.5 at % and 0.4 at % < y < 7.6 at %.

Other properties i.e. saturation magnetization, Ms and resistivity,  $\rho$  largely unaffected

## References

- [1] D. S. Gardner et al., IEEE International electron device meeting, (IEDM), San Francisco (USA), 11-13 December 2006
- [2] S. Roy et al. J. Magn. Mag. Mater, 290-291, 1524 (2005).
- [3] J.M. Riveiro et al, IEEE Trans. Mag., 16, 1426 (1980).
- [4] J.M. Riveiro, G. Riveiro, IEEE Trans. Mag., 17, No. 6, 3082 (1981).
- [5] L.Perez et al, Sens. Act. A 109 208 (2004)
- [6] Oda et al, US Patent 584494A (1996)
- [7] A.Brenner, "Electrodeposition of Alloys", Academic Press, London 1963